

# Norifumi Fujimura

## List of Publications by Year in descending order

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164  
papers

2,974  
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g-index

164  
all docs

164  
docs citations

164  
times ranked

2462  
citing authors

#	ARTICLE	IF	CITATIONS
1	Control of preferred orientation for ZnOx films: control of self-texture. Journal of Crystal Growth, 1993, 130, 269-279.	0.7	665
2	Epitaxially grown YMnO3 film: New candidate for nonvolatile memory devices. Applied Physics Letters, 1996, 69, 1011-1013.	1.5	303
3	Ferroelectric properties of YMnO3 epitaxial films for ferroelectric-gate field-effect transistors. Journal of Applied Physics, 2003, 93, 5563-5567.	1.1	105
4	Growth mechanism of YMnO3 film as a new candidate for nonvolatile memory devices. Journal of Applied Physics, 1996, 80, 7084-7088.	1.1	94
5	Structural, dielectric, and magnetic properties of epitaxially grown BaFeO3 thin films on (100) SrTiO3 single-crystal substrates. Applied Physics Letters, 2002, 81, 2764-2766.	1.5	89
6	Characterization of ferroelectricity in metal/ferroelectric/insulator/semiconductor structure by pulsed C-V measurement; Ferroelectricity in YMnO3/Y2O3/Si structure. Journal of Applied Physics, 2000, 87, 3444-3449.	1.1	72
7	Direct piezoelectric properties of (100) and (111) BiFeO3 epitaxial thin films. Applied Physics Letters, 2012, 100, 102901.	1.5	69
8	Ferroelectric properties of c-oriented YMnO3 films deposited on Si substrates. Applied Physics Letters, 1998, 73, 414-416.	1.5	60
9	Raman scattering studies on multiferroic YMnO <sub>3</sub> . Journal of Physics Condensed Matter, 2007, 19, 365239.	0.7	55
10	Ferroelectricity of YMnO3 thin films prepared via solution. Applied Physics Letters, 1999, 75, 719-721.	1.5	54
11	Formation of two-dimensional electron gas and the magnetotransport behavior of ZnMnO/ZnO heterostructure. Journal of Applied Physics, 2003, 93, 7673-7675.	1.1	53
12	Ferromagnetic and ferroelectric behaviors of A-site substituted YMnO3-based epitaxial thin films. Journal of Applied Physics, 2003, 93, 6990-6992.	1.1	44
13	Magnetic properties of highly resistive BaFeO3 thin films epitaxially grown on SrTiO3 single-crystal substrates. Journal of Applied Physics, 2003, 93, 6993-6995.	1.1	40
14	LiNbO3 film with a new epitaxial orientation on R-cut sapphire. Journal of Applied Physics, 1994, 75, 2169-2176.	1.1	37
15	Piezoelectric Vibrational Energy Harvester Using Lead-Free Ferroelectric BiFeO <sub>3</sub> Films. Applied Physics Express, 2013, 6, 051501.	1.1	37
16	Effect of Oxygen Deficiencies on Magnetic Properties of Epitaxial Grown BaFeO <sub>3</sub> Thin Films on. IEEE Transactions on Magnetics, 2004, 40, 2736-2738.	1.2	35
17	Electrical Characteristics of Controlled-Polarization-Type Ferroelectric-Gate Field-Effect Transistor. Japanese Journal of Applied Physics, 2008, 47, 8874.	0.8	35
18	Influence of Schottky and Poole-Frenkel emission on the retention property of YMnO3-based metal/ferroelectric/insulator/semiconductor capacitors. Journal of Applied Physics, 2003, 94, 4036-4041.	1.1	34

#	ARTICLE	IF	CITATIONS
19	Improvement of magnetization and leakage current properties of magnetoelectric BaFeO <sub>3</sub> thin films by Zr substitution. Applied Physics Letters, 2005, 86, 082902.	1.5	33
20	Influence of antiferromagnetic exchange interaction on magnetic properties of ZnMnO thin films grown pseudomorphically on ZnO (0001Å) single-crystal substrates. Journal of Applied Physics, 2008, 103, .	1.1	33
21	The effects of Xe on an rf plasma and growth of ZnO films by rf sputtering. Journal of Applied Physics, 2004, 95, 3923-3927.	1.1	32
22	Pulsed-Laser-Deposited YMnO <sub>3</sub> Epitaxial Films with Square Polarization-Electric Field Hysteresis Loop and Low-Temperature Growth. Japanese Journal of Applied Physics, 2004, 43, 6613-6616.	0.8	31
23	Systematic Study of Photoluminescence Enhancement in Monolayer Molybdenum Disulfide by Acid Treatment. Langmuir, 2018, 34, 10243-10249.	1.6	29
24	Effect of substitutionally dissolved Ce in Si on the magnetic and electric properties of magnetic semiconductor Si <sub>1-x</sub> Ce <sub>x</sub> films. Applied Physics Letters, 2002, 81, 4023-4025.	1.5	28
25	Epitaxial growth of CuScO <sub>2</sub> thin films on sapphire a-plane substrates by pulsed laser deposition. Journal of Applied Physics, 2005, 97, 083535.	1.1	25
26	Photoluminescence properties peculiar to the Mn-related transition in a lightly alloyed ZnMnO thin film grown by pulsed laser deposition. Applied Physics Letters, 2006, 88, 241908.	1.5	24
27	Photoactivation of Strong Photoluminescence in Superacid-Treated Monolayer Molybdenum Disulfide. ACS Applied Materials & Interfaces, 2020, 12, 36496-36504.	4.0	24
28	Detailed structural analysis of Ce doped Si thin films. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 237-241.	1.3	22
29	Microstructure and Dielectric Properties of YMnO <sub>3</sub> Thin Films Prepared by Dip-Coating. Journal of the American Ceramic Society, 1998, 81, 1357-1360.	1.9	20
30	Multiferroic behaviour of YMnO <sub>3</sub> and YbMnO <sub>3</sub> epitaxial films. Philosophical Magazine Letters, 2007, 87, 193-201.	0.5	20
31	Analysis of nitrogen plasma generated by a pulsed plasma system near atmospheric pressure. Journal of Applied Physics, 2004, 96, 6094-6096.	1.1	19
32	Development of Piezoelectric MEMS Vibration Energy Harvester Using (100) Oriented BiFeO <sub>3</sub> Ferroelectric Film. Journal of Physics: Conference Series, 2013, 476, 012007.	0.3	19
33	Enhancement of piezoelectric properties of (100)-orientated BiFeO <sub>3</sub> films on (100)LaNiO <sub>3</sub> /Si. Japanese Journal of Applied Physics, 2014, 53, 09PA14.	0.8	19
34	Strain Dependent Electronic Structure and Band Offset Tuning at Heterointerfaces of A <sub>2</sub> SnO <sub>3</sub> (A=Ca, Sr, Ba) / SrTiO <sub>3</sub> . Applied Physics Letters, 2016, 109, 162101.	1.6	19
35	Demonstration of high-performance piezoelectric MEMS vibration energy harvester using BiFeO <sub>3</sub> film with improved electromechanical coupling factor. Sensors and Actuators A: Physical, 2019, 291, 167-173.	2.0	19
36	Electro-optical effect in ZnO:Mn thin films prepared by Xe sputtering. Journal of Applied Physics, 2006, 99, 013509.	1.1	18

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37	Time-Dependent Imprint in $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ Ferroelectric Thin Films. <i>Advanced Electronic Materials</i> , 2021, 7, 2100151.	2.6	18
38	Electro-Optic Effect in Epitaxial ZnO:Mn Thin Films. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 6916-6918.	0.8	17
39	Reaction of Si with excited nitrogen species in pure nitrogen plasma near atmospheric pressure. <i>Thin Solid Films</i> , 2006, 506-507, 423-426.	0.8	16
40	Preparation and Dielectric Properties of $\text{YMnO}_3$ Ferroelectric Thin Films by the Sol-Gel Method. <i>Journal of Sol-Gel Science and Technology</i> , 1998, 13, 903-908.	1.1	15
41	Preparation and the magnetic property of $\text{ZnMnO}$ thin films on ZnO single crystal substrate. <i>Journal of Magnetism and Magnetic Materials</i> , 2007, 310, e711-e713.	1.0	15
42	Electromechanical characteristics of piezoelectric vibration energy harvester with 2-degree-of-freedom system. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	15
43	Effect of carrier for magnetic and magnetotransport properties of Si:Ce films. <i>Journal of Applied Physics</i> , 2003, 93, 7679-7681.	1.1	14
44	Magnetic and magnetotransport properties of solid phase epitaxially grown Si:Ce films. <i>Journal of Applied Physics</i> , 2003, 93, 4045-4048.	1.1	14
45	Electro-optic effect in ZnO:Mn thin films. <i>Journal of Alloys and Compounds</i> , 2004, 371, 157-159.	2.8	14
46	Detailed structural analysis and dielectric properties of silicon nitride film fabricated using pure nitrogen plasma generated near atmospheric pressure. <i>Journal of Applied Physics</i> , 2006, 100, 073710.	1.1	14
47	Analysis of carrier modulation in channel of ferroelectric-gate transistors having polar semiconductor. <i>Thin Solid Films</i> , 2010, 518, 3026-3029.	0.8	14
48	Impedance Analysis of Controlled-Polarization-Type Ferroelectric-Gate Thin Film Transistor Using Resistor-Capacitor Lumped Constant Circuit. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DD16.	0.8	14
49	Synthesis of $\text{Bi}(\text{Fe}_x\text{Al}_{1-x})\text{O}_3$ Thin Films by Pulsed Laser Deposition and Its Structural Characterization. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 6609-6612.	0.8	13
50	Ferromagnetic and dielectric behavior of mn-doped $\text{BaCoO}_3$ . <i>IEEE Transactions on Magnetics</i> , 2005, 41, 3496-3498.	1.2	13
51	Growth and Ferromagnetic Properties of Ferroelectric $\text{YbMnO}_3$ Thin Films. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 7329-7331.	0.8	12
52	Magnetic frustration behavior of ferroelectric ferromagnet $\text{YbMnO}_3$ epitaxial films. <i>Journal of Applied Physics</i> , 2007, 101, 09M107.	1.1	12
53	Polarization Switching Behavior of $\text{YMnO}_3$ Thin Film at around Magnetic Phase Transition Temperature. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 09KB05.	0.8	12
54	Title is missing!. <i>Journal of Sol-Gel Science and Technology</i> , 2000, 19, 589-593.	1.1	11

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55	Ce concentration dependence on the magnetic and transport properties of Ce doped Si epitaxial films prepared by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2002, 91, 7905.	1.1	11
56	Piezoelectric properties of (100) orientated BiFeO <sub>3</sub> thin films on LaNiO <sub>3</sub> . <i>Japanese Journal of Applied Physics</i> , 2014, 53, 08NB02.	0.8	11
57	Enhancement of ferromagnetic ordering in dielectric BaFe <sub>1-x</sub> Zr <sub>x</sub> O <sub>3</sub> (x=0.5~0.8) single-crystal films by pulsed laser-beam deposition. <i>Journal of Applied Physics</i> , 2005, 97, 10M509.	1.1	10
58	Magnetic properties of low-temperature grown Si:Ce thin films on (001) Si substrate. <i>Journal of Magnetism and Magnetic Materials</i> , 2007, 310, e726-e728.	1.0	10
59	Contribution of s-d exchange interaction to magnetoresistance of ZnO-based heterostructures with a magnetic barrier. <i>Physical Review B</i> , 2009, 80, .	1.1	10
60	Enhancement of Direct Piezoelectric Properties of Domain-Engineered (100) BiFeO <sub>3</sub> Films. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 09KA03.	0.8	10
61	Correlation between the intra-atomic Mn <sup>3+</sup> photoluminescence and antiferromagnetic transition in an YMnO <sub>3</sub> epitaxial film. <i>Applied Physics Express</i> , 2014, 7, 023002.	1.1	10
62	Piezoelectric energy harvesting from AC current-carrying wire. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SLLD10.	0.8	10
63	Exotic Doping for ZnO Thin Films: Possibility of Monolithic Optical Integrated Circuit. <i>Materials Research Society Symposia Proceedings</i> , 1999, 574, 317.	0.1	9
64	Structural analysis and electrical properties of pure Ge <sub>3</sub> N <sub>4</sub> dielectric layers formed by an atmospheric-pressure nitrogen plasma. <i>Journal of Applied Physics</i> , 2011, 110, 064103.	1.1	9
65	Lowering the growth temperature of strongly-correlated YbFe <sub>2</sub> O <sub>4</sub> thin films prepared by pulsed laser deposition. <i>Thin Solid Films</i> , 2016, 614, 44-46.	0.8	9
66	Investigation of mechanical nonlinear effect in piezoelectric MEMS vibration energy harvesters. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 11UD03.	0.8	9
67	Growth process observation of homoepitaxial ZnO thin films using optical emission spectra during pulsed laser deposition. <i>Thin Solid Films</i> , 2010, 518, 2971-2974.	0.8	8
68	Interface energetics and atomic structure of epitaxial La <sub>1-x</sub> Sr <sub>x</sub> CoO <sub>3</sub> on Nb:SrTiO <sub>3</sub> . <i>Applied Physics Letters</i> , 2015, 106, .	1.5	8
69	The effects of small amounts of oxygen during deposition on structural changes in sputtered HfO <sub>2</sub> -based films. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SLLB03.	0.8	8
70	Ultralarge Photoluminescence Enhancement of Monolayer Molybdenum Disulfide by Spontaneous Superacid Nanolayer Formation. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 25280-25289.	4.0	8
71	Formation of Silicon Oxynitride Films with Low Leakage Current Using N <sub>2</sub> /O <sub>2</sub> Plasma near Atmospheric Pressure. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 7853-7856.	0.8	7
72	Optical propagation loss of ZnO films grown on sapphire. <i>Journal of Applied Physics</i> , 2004, 95, 1673-1676.	1.1	7

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73	Spin-dependent transport in a ZnMnO <sub>2</sub> /ZnO heterostructure. Journal of Applied Physics, 2008, 103, 07D124.	1.1	7
74	Magnetic Properties of Uniformly Ce-Doped Si Thin Films with n-Type Conduction. Japanese Journal of Applied Physics, 2009, 48, 033003.	0.8	7
75	Surface preparation of ZnO single-crystal substrate for the epitaxial growth of ZnO thin films. Journal of Crystal Growth, 2011, 318, 516-518.	0.7	7
76	Evaluation of the electronic states in highly Ce doped Si films grown by low temperature molecular beam epitaxy system. Journal of Crystal Growth, 2015, 425, 158-161.	0.7	7
77	Growth and ferroelectric properties of La and Al codoped BiFeO <sub>3</sub> epitaxial films. Journal of Applied Physics, 2017, 121, 174102.	1.1	7
78	Effect of Additional Oxygen on Formation of Silicon Oxynitride Using Nitrogen Plasma Generated near Atmospheric Pressure. Japanese Journal of Applied Physics, 2006, 45, 9025-9028.	0.8	6
79	Influence of antiferromagnetic ordering on ferroelectric polarization switching of YMnO <sub>3</sub> /epitaxial thin films. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2007, 54, 2641-2644.	1.7	6
80	The comparison of the growth models of silicon nitride ultrathin films fabricated using atmospheric pressure plasma and radio frequency plasma. Journal of Applied Physics, 2007, 101, 023513.	1.1	6
81	Low temperature growth of Si:Ce thin films with high crystallinity and uniform distribution of Ce grown by solid-source molecular beam epitaxy. Journal of Crystal Growth, 2007, 307, 30-34.	0.7	6
82	Electron transport properties of Zn <sub>0.88</sub> Mn <sub>0.12</sub> O <sub>2</sub> /ZnO modulation-doped heterostructures. Journal of Vacuum Science & Technology B, 2009, 27, 1760.	1.3	6
83	Impedance Analysis of Controlled-Polarization-Type Ferroelectric-Gate Thin Film Transistor Using Resistor-Capacitor Lumped Constant Circuit. Japanese Journal of Applied Physics, 2011, 50, 04DD16.	0.8	6
84	Effect of the annealing temperature of P(VDF/TrFE) thin films on their ferroelectric properties. Journal of the Korean Physical Society, 2013, 62, 1065-1068.	0.3	6
85	Ultrafast dynamics of coherent optical phonon correlated with the antiferromagnetic transition in a hexagonal YMnO <sub>3</sub> epitaxial film. Applied Physics Letters, 2017, 111, .	1.5	6
86	Investigation of the wake-up process and time-dependent imprint of Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> film through the direct piezoelectric response. Applied Physics Letters, 2021, 119, .	1.5	6
87	Investigation of efficient piezoelectric energy harvesting from impulsive force. Japanese Journal of Applied Physics, 2020, 59, SPPD04.	0.8	6
88	Effect of Ferroelectric Polarization on Carrier Transport in Controlled Polarization-Type Ferroelectric Gate Field-Effect Transistors with Poly(vinylidene fluoride-tetrafluoroethylene)/ZnO Heterostructure. Japanese Journal of Applied Physics, 2012, 51, 11PB01.	0.8	6
89	Orientation control of (Ca,Sr)CuO <sub>2</sub> thin films. Journal of Applied Physics, 1995, 77, 3805-3811.	1.1	5
90	Dielectric properties of ferroelectric/DMS heterointerface using YMnO <sub>3</sub> and Ce doped Si. Applied Surface Science, 2008, 254, 6218-6221.	3.1	5

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91	Aluminum-doped zinc oxide electrode for robust (Pb,La)(Zr,Ti)O <sub>3</sub> capacitors: effect of oxide insulator encapsulation and oxide buffer layer. <i>Journal of Materials Science: Materials in Electronics</i> , 2014, 25, 2155-2161.	1.1	5
92	Al:ZnO top electrodes deposited with various oxygen pressures for ferroelectric (Pb,La)(Zr,Ti)O <sub>3</sub> capacitors. <i>Electronics Letters</i> , 2016, 52, 230-232.	0.5	5
93	The effect of crystal distortion and domain structure on piezoelectric properties of BiFeO <sub>3</sub> thin films. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 11UF07.	0.8	5
94	Valence states and the magnetism of Eu ions in Eu-doped GaN. <i>Journal of Applied Physics</i> , 2020, 127, 083901.	1.1	5
95	Control of Crystal Structure of BiFeO <sub>3</sub> Epitaxial Thin Films by Adjusting Growth Conditions and Piezoelectric Properties. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 09LB04.	0.8	5
96	Dissolution pits and Si epitaxial regrowth in the Al/(111)Si system. <i>Journal of Applied Physics</i> , 1988, 64, 4499-4502.	1.1	4
97	Magnetic and Ferroelectric Properties of YMnO <sub>3</sub> Epitaxial Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 2006, 966, 1.	0.1	4
98	The effects of aluminum doping for the magnetotransport property of Si:Ce thin films. <i>Journal of Applied Physics</i> , 2010, 107, 09C308.	1.1	4
99	Orientation Control of ZnO Films Deposited Using Nonequilibrium Atmospheric Pressure N <sub>2</sub> /O <sub>2</sub> Plasma. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 01AC03.	0.8	4
100	Improved reliability properties of (Pb,La)(Zr,Ti)O <sub>3</sub> ferroelectric capacitors by thin aluminium-doped zinc oxide buffer layer. <i>Electronics Letters</i> , 2014, 50, 799-801.	0.5	4
101	Near-surface structure of polar ZnO surfaces prepared by pulsed laser deposition. <i>Thin Solid Films</i> , 2014, 559, 88-91.	0.8	4
102	Crystallographic polarity effect of ZnO on thin film growth of pentacene. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 04CJ03.	0.8	4
103	Reaction of N,N-dimethylformamide and divalent viologen molecule to generate an organic dopant for molybdenum disulfide. <i>AIP Advances</i> , 2018, 8, 055313.	0.6	4
104	Quantitative analysis of the direct piezoelectric response of bismuth ferrite films by scanning probe microscopy. <i>Scientific Reports</i> , 2019, 9, 19727.	1.6	4
105	Change in the defect structure of composition controlled single-phase YbFe <sub>2</sub> O <sub>4</sub> epitaxial thin films. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SPPB07.	0.8	4
106	Structural control of nonequilibrium WSi <sub>2.6</sub> thin films by external stress. <i>Journal of Applied Physics</i> , 1993, 73, 733-739.	1.1	3
107	Mechanism for ordering in SiGe films with reconstructed surface. <i>Applied Physics Letters</i> , 1997, 71, 1174-1176.	1.5	3
108	YMnO <sub>3</sub> and YbMnO <sub>3</sub> Thin Films for fet type FeRam Application. <i>Materials Research Society Symposia Proceedings</i> , 1999, 574, 237.	0.1	3



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109	Origin of Leakage Current of YMnO <sub>3</sub> Thin Films Prepared by the Sol-Gel Method. Materials Research Society Symposia Proceedings, 1999, 596, 481.	0.1	3
110	Effect of plasma-induced damage on interfacial reactions of titanium thin films on silicon surfaces. Applied Physics Letters, 2000, 76, 2358-2360.	1.5	3
111	Effects of spontaneous and piezoelectric polarizations on carrier confinement at the Zn <sub>0.88</sub> Mn <sub>0.12</sub> O/ZnO interface. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3107-3109.	0.8	3
112	Novel chemical vapor deposition process of ZnO films using nonequilibrium N <sub>2</sub> plasma generated near atmospheric pressure with small amount of O <sub>2</sub> below 1%. Journal of Applied Physics, 2016, 119, 175302.	1.1	3
113	Reliability of the Properties of (Pb,La)(Zr,Ti)O <sub>3</sub> Capacitors with Non-noble Metal Oxide Electrodes stored in an H <sub>2</sub> Atmosphere. MRS Advances, 2016, 1, 369-374.	0.5	3
114	Tuning Transition-Metal Dichalcogenide Field-Effect Transistors by Spontaneous Pattern Formation of an Ultrathin Molecular Dopant Film. ACS Nano, 2018, 12, 10123-10129.	7.3	3
115	Electronic Structure Mosaicity of Monolayer Transition Metal Dichalcogenides by Spontaneous Pattern Formation of Donor Molecules. ACS Applied Materials & Interfaces, 2019, 11, 15922-15926.	4.0	3
116	Time-resolved simulation of the negative capacitance stage emerging at the ferroelectric/semiconductor hetero-junction. AIP Advances, 2019, 9, 025037.	0.6	3
117	Metallic Transport in Monolayer and Multilayer Molybdenum Disulfides by Molecular Surface Charge Transfer Doping. ACS Applied Materials & Interfaces, 2022, , .	4.0	3
118	Solid phase reactions and change in stress of TiN/Ti/Si for a diffusion barrier. Journal of Applied Physics, 1990, 67, 2899-2903.	1.1	2
119	Formation of (1120) ZnO Films by Controlling the Selftexture and the Relaxation of Film Stress. Materials Research Society Symposia Proceedings, 1992, 263, 297.	0.1	2
120	The Progress of YMnO <sub>3</sub> /Y <sub>2</sub> O <sub>3</sub> /Si System for a Ferroelectric Gate Field Effect Transistor. Ferroelectrics, 2002, 271, 229-234.	0.3	2
121	Magnetic and dielectric properties of Yb(Mn <sub>1-x</sub> Al <sub>x</sub> )O <sub>3</sub> thin films. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2008, 55, 1056-1060.	1.7	2
122	Effects of La substitution for BiFeO <sub>3</sub> epitaxial thin films. Journal of the Korean Physical Society, 2013, 62, 1069-1072.	0.3	2
123	Fabrication and Characterization of (Ba,La)SnO <sub>3</sub> Semiconducting Epitaxial Films on (111) and (001) SrTiO <sub>3</sub> Substrates. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1700800.	0.8	2
124	Strong Photoluminescence Enhancement from Bilayer Molybdenum Disulfide via the Combination of UV Irradiation and Superacid Molecular Treatment. Applied Sciences (Switzerland), 2021, 11, 3530.	1.3	2
125	Ce-Induced Reconstruction of Si(001) Surface Structures. Japanese Journal of Applied Physics, 2011, 50, 065701.	0.8	2
126	Detailed C-V Analysis for YbMnO <sub>3</sub> /Y <sub>2</sub> O <sub>3</sub> /Si Structure. Materials Research Society Symposia Proceedings, 1999, 574, 359.	0.1	1



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127	The Effect of Leakage Current on the Retention Property of YMnO <sub>3</sub> Based MFIS Capacitor. Integrated Ferroelectrics, 2002, 49, 41-49.	0.3	1
128	Interface characteristics of (Zn,Mn)O/ZnO grown on ZnO substrate. Journal of Crystal Growth, 2005, 275, e2211-e2215.	0.7	1
129	Influence of Antiferromagnetic Ordering on Ferroelectric Polarization Switching of YMnO <sub>3</sub> ; Epitaxial Thin Films. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	1
130	Electro-optic property of ZnO:Mn epitaxial films. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3110-3112.	0.8	1
131	Ferroelectric Properties of Magnetoferroelectric YMnO <sub>3</sub> Epitaxial Films at around the Neel Temperature. Key Engineering Materials, 2010, 445, 144-147.	0.4	1
132	Effect of Lattice Misfit Strain on Crystal System and Ferroelectric Property of BiFeO <sub>3</sub> Epitaxial Thin Films. IOP Conference Series: Materials Science and Engineering, 2011, 18, 092064.	0.3	1
133	Electronic Transport in Organic Ferroelectric Gate Field-Effect Transistors with ZnO Channel. Materials Research Society Symposia Proceedings, 2012, 1430, 19.	0.1	1
134	Effects of polarization of polar semiconductor on electrical properties of poly(vinylidene fluoride)/ferroelectric thin film heterostructure. Journal of Applied Physics, 2010, 107, 462-462.	1.1	1
135	Low temperature formation of highly resistive ZnO films using nonequilibrium N <sub>2</sub> /O <sub>2</sub> plasma generated near atmospheric pressure. Thin Solid Films, 2016, 616, 415-418.	0.8	1
136	Cerium ion doping into self-assembled Ge using three-dimensional dot structure. Journal of Crystal Growth, 2017, 468, 696-700.	0.7	1
137	High efficiency piezoelectric MEMS vibrational energy harvesters using (100) oriented BiFeO <sub>3</sub> films. , 2017, , .		1
138	Fabrication of chemical composition controlled YbFe <sub>2</sub> O <sub>4</sub> epitaxial thin films. Japanese Journal of Applied Physics, 2019, 58, SLLB11.	0.8	1
139	Correlation between photoluminescence and antiferromagnetic spin order in strongly correlated YMnO <sub>3</sub> ferroelectric epitaxial thin film. AIP Advances, 2021, 11, 075122.	0.6	1
140	Fabrication of YMnO <sub>3</sub> Films: New Candidate for Non-Volatile Memory Devices. Materials Research Society Symposia Proceedings, 1996, 433, 119.	0.1	0
141	Effect of carrier concentration on the magnetic behavior of ferroelectric YMnO <sub>3</sub> ceramics and thin films. , 0, , .		0
142	Effect of A-site substitution on the magnetic and dielectric behaviors of YMnO <sub>3</sub> based ferroelectric thin films. , 0, , .		0
143	Investigation of Retention Properties for YMnO <sub>3</sub> Based Metal/Ferroelectric/Insulator/Semiconductor Capacitors. Materials Research Society Symposia Proceedings, 2003, 784, 971.	0.1	0
144	Investigation of Retention Properties for YMnO <sub>3</sub> Based Metal/Ferroelectric/Insulator/Semiconductor Capacitors. Materials Research Society Symposia Proceedings, 2003, 786, 971.	0.1	0

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145	Fabrication of Silicon Nitride Film using Pure Nitrogen Plasma Generated near Atmospheric Pressure for III-V Semiconductor Fabrication. Materials Research Society Symposia Proceedings, 2004, 831, 144.	0.1	0
146	Magnetic properties of low temperature grown Si:Ce thin films on [001] Si substrate by molecular beam epitaxy. , 2005, , .		0
147	Ferromagnetic and dielectric behavior of Mn doped BaCoO/sub 3/. , 2005, , .		0
148	Magnetic properties of Er,O-codoped GaAs at low temperature. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4082-4085.	0.8	0
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